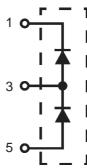


Dual Power Schottky Diode

in ISOPLUS i4-PAC™

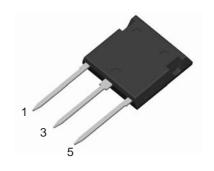
FSS 100-008A

= 80 V= 0.9 V $I_{F(AV)M} = 90 A$



			L	'	
Diodes					
Symbol	Conditions		Maximum Ratings		
V_{RRM}			80	V	
I _{FAV}	$T_{c} = 90^{\circ}C$; sine $T_{c} = 90^{\circ}C$; d = 0		85 90	A A	
P _{tot}	T _C = 25°C	(per diode)	100	W	

Symbol	Conditions	Characteristic Values $(T_{VJ} = 25^{\circ}C, \text{ unless otherwise specified})$ min. typ. max.		
V _F	I _F = 75 A; T _{VJ} = 25°C T _{VJ} = 125°C		0.9 0.8	1.0 V
I _R	$V_R = V_{RRM}$; $T_{VJ} = 25$ °C $T_{VJ} = 125$ °C		2.5	2 mA mA
R _{thJC}	(per diode)			1.4 K/W



Features

- · Schottky diodes
- very low forward voltage
- extremely fast switching
- blocking capability optimized for elevated temperature
- ISOPLUS i4-PAC™ package
- DCB isolated back surface
- enlarged creepage towards heatsink
- application friendly pinout
- low inductive current path
- high reliability
- industry standard outline

Applications

- for use in
 - automotive drives and converters
 - hand held tools
 - low voltage power supplies
 - battery chargers
 - solar converters
- operating
- as free wheeling diode of choppers for supply of motors or transformers
- as high frequency secondary rectifier
- anti paralleled to MOSFETs complementing their intrinsic body diode

Recommended replacement: DSSS 35-008AR

Data according to IEC 60747 and refer to a single diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.



Component				
Symbol	Conditions	Maximum Ratings		
T _{VJ} T _{stg}		-55+175 -55+125	°C	
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500	V~	
F _c	mounting force with clip	20120	N	

Symbol	Conditions	Ch	Characteristic Values		
		min.	typ.	max.	
C _P	coupling capacity between shorted pins and mounting tab in the case		40	pF	
d _s , d _a d _s , d _a	pin - pin pin - backside metal	5.5 5.5		mm mm	
R _{thCH}	with heatsink compound		0.15	K/W	
Weight			9	g	

